

DERWENT-ACC-NO: 2001-229584

DERWENT-WEEK: 200124

COPYRIGHT 1999 DERWENT INFORMATION LTD

TITLE: Semiconductor device manufacture involves forming
indium
gallium phosphide layer on gallium arsenide layer and
etching indium gallium phosphide layer using hydrochloric
acid etching liquid or its aqueous solution

PATENT-ASSIGNEE: NEC CORP[NIDE]

PRIORITY-DATA: 1999JP-0198228 (July 12, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES
MAIN-IPC			
JP 2001023951 A 021/306	January 26, 2001	N/A	007 H01L

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
JP2001023951A	N/A	1999JP-0198228	July 12, 1999

INT-CL (IPC): C09K013/04, H01L021/306 , H01L021/308 , H01L033/00

ABSTRACTED-PUB-NO: JP2001023951A

BASIC-ABSTRACT: